

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	270	mA
		V _{GS} = 10 V; T _{sp} = 25 °C		-	-	330	mA
Static charact	eristics		-				,
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 200 mA; T _j = 25 °C		-	2.2	2.8	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G G S S 017aaa255

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
NX7002BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
NX7002BK	%4R

[1] % = placeholder for manufacturing site code

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8. Limiting values

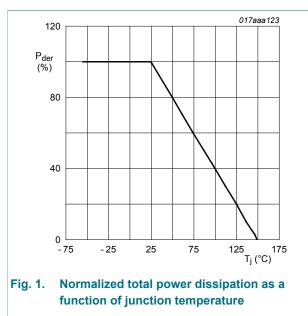
Table 5.Limiting values

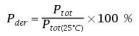
In accordance with the Absolute Maximum Rating System (IEC 60134).

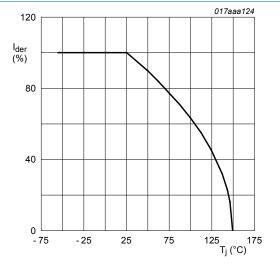
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
ID	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	270	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{sp} = 25 °C		-	330	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	0.9	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode		1			
ls	source current	T _{amb} = 25 °C	[1]	-	200	mA

Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard for the standard

footprint.







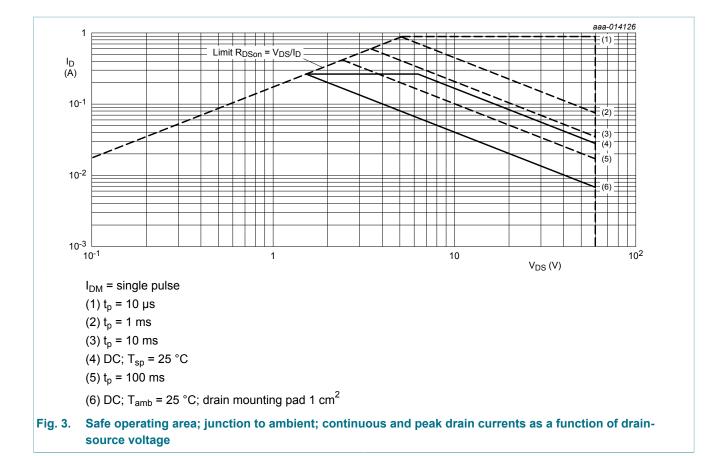


$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

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9. Thermal characteristics

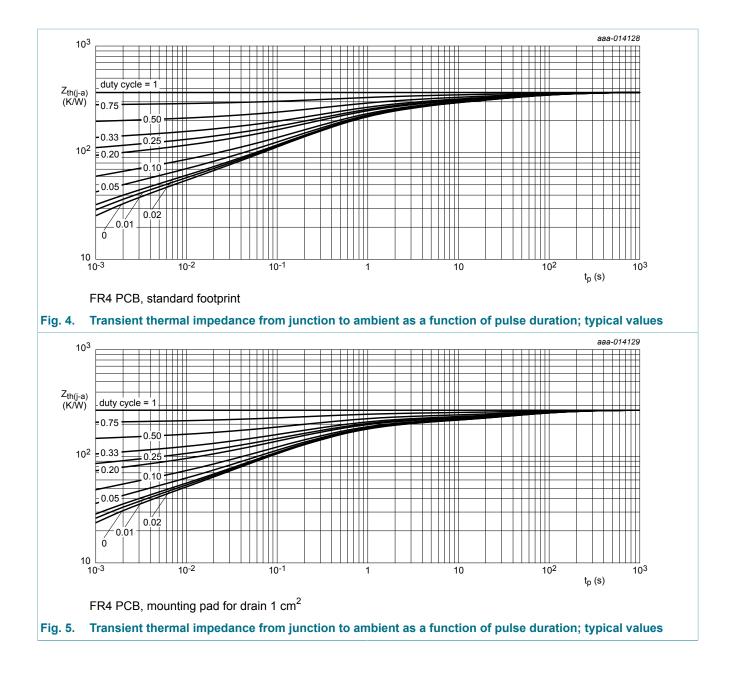
Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	350	405	K/W
			[2]	-	270	310	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

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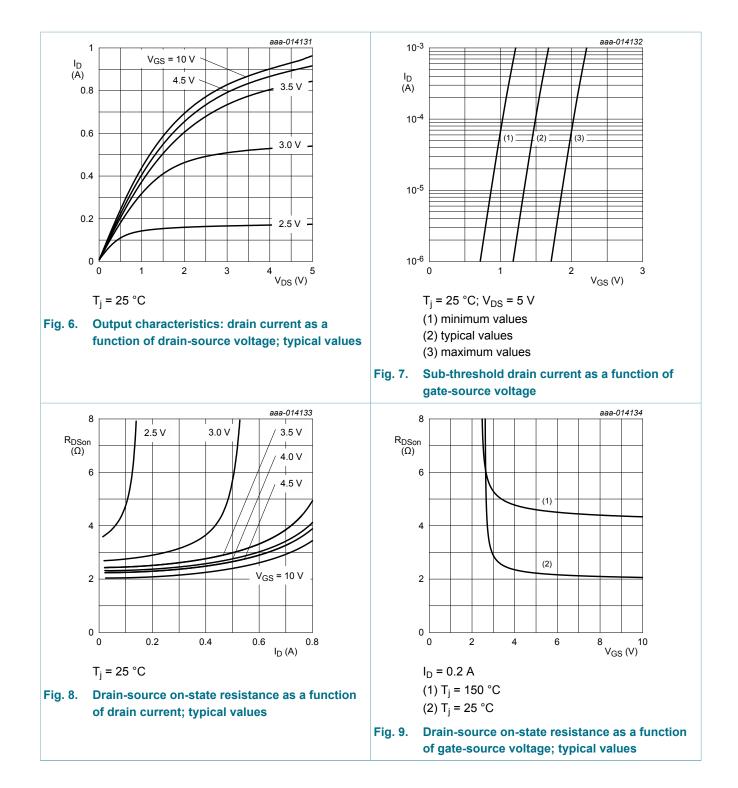
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	1				
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μA
		V_{GS} = -5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.3	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	2.2	2.8	Ω
		V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	4.5	5.7	Ω
		V _{GS} = 5 V; I _D = 200 mA; T _j = 25 °C	-	2.5	3.2	Ω
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	600	-	mS
R _G	internal gate resistance (AC)	f = 2.5 MHz	-	2.5	-	Ω
Dynamic ch	aracteristics	· · ·				
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I _D = 200 mA; V _{GS} = 10 V;	-	1	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q _{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	23.6	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.6	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; I _D = 200 mA; V _{GS} = 10 V;	-	4.7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t _{d(off)}	turn-off delay time	1	-	6.9	-	ns
t _f	fall time	1	-	2.9	-	ns
Source-drai	n diode	· · ·	1		-1	
V _{SD}	source-drain voltage	I _S = 200 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.87	1.2	V

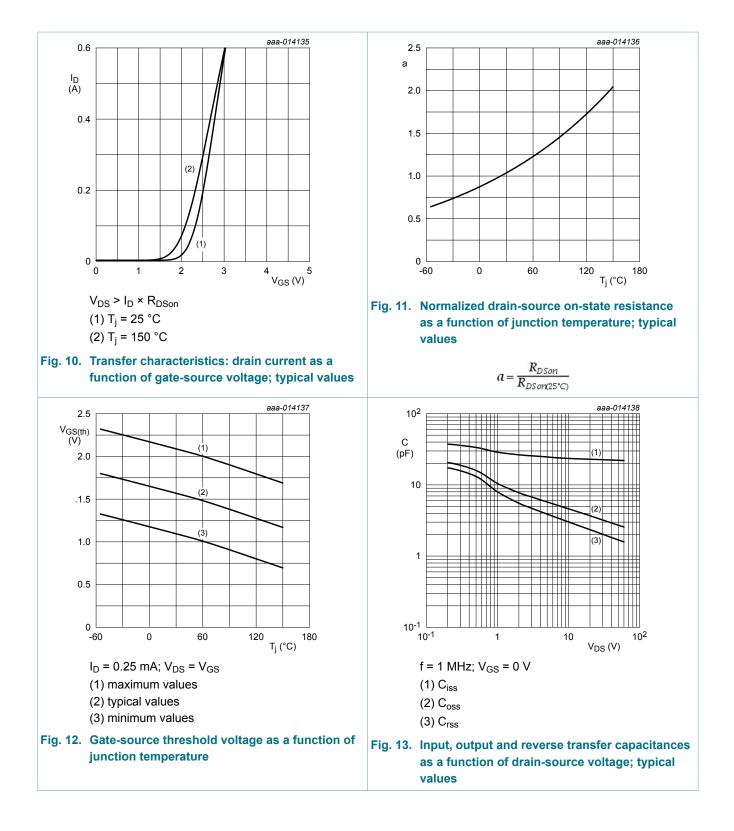
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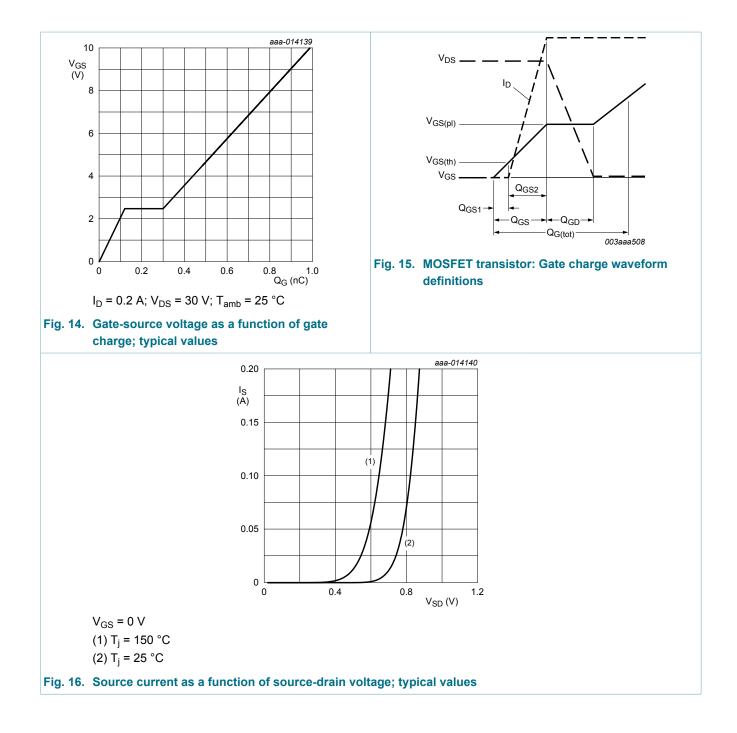


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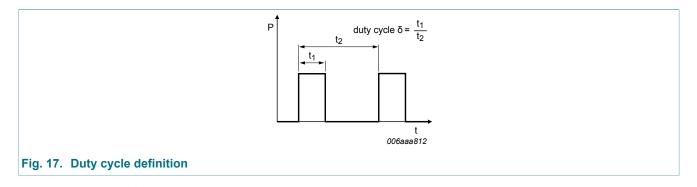
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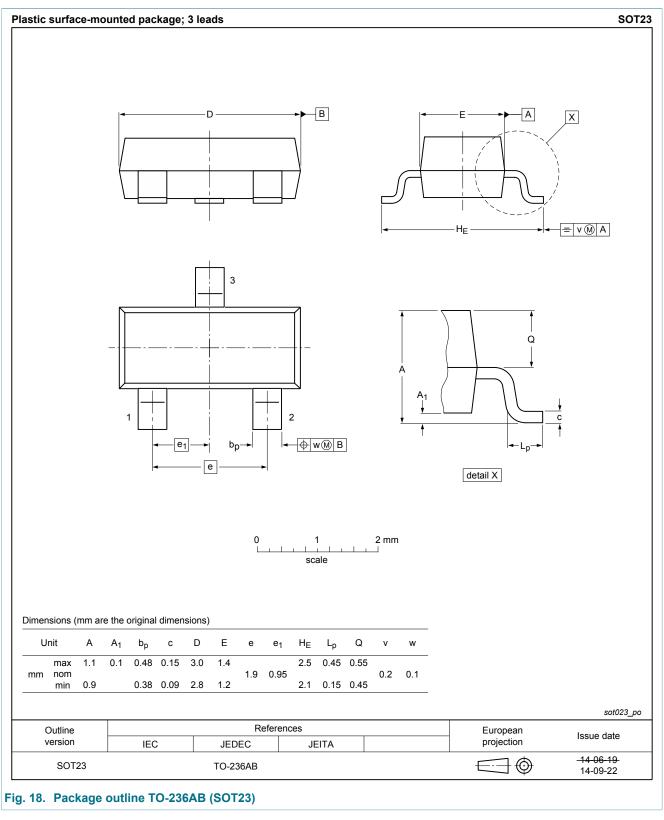
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11. Test information



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12. Package outline

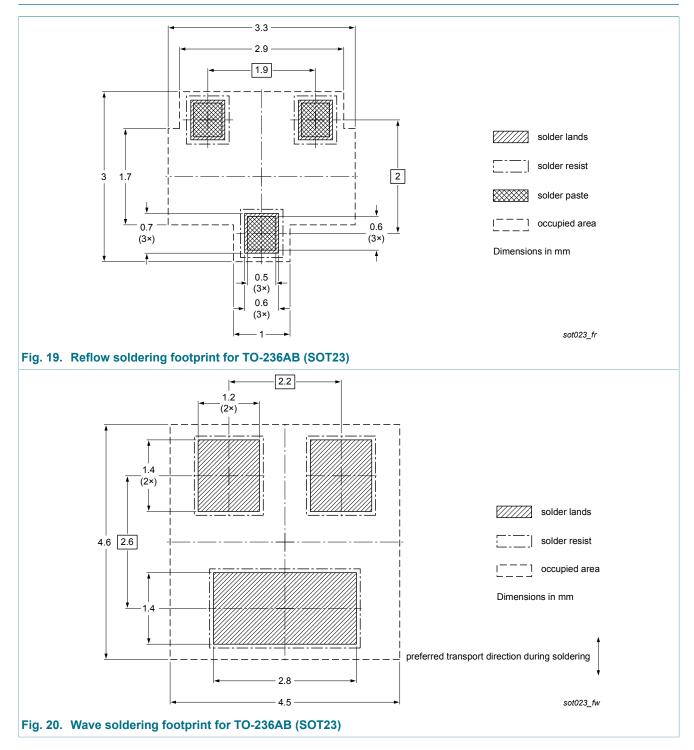


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13. Soldering



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14. Revision history

Table 8. Revision his	story						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX7002BK v.3	20150512	Product data sheet	-	NX7002BK v.2			
Modifications:	 Table 1 and 5: added drain current I_D at T_{sp}= 25 °C Flgure 3: corrected figure notes 						
NX7002BK v.2	20150429	Product data sheet	-	NX7002BK v.1			
NX7002BK v.1	20140808	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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